Supporting Information

Wafer-scale porous GaN single crystal substrates and its application in energy storage

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SEM characterization of porous GaN

Figure S1. Surface and cross section SEM images of porous GaN samples annealed at 1150 °C for different times (a, b) 45min, (c, d) 75min, (e, f) 90 min.
High-resolution X-ray diffraction (HRXRD) rocking curves of as grown GaN and porous GaN samples

Figure S2. High-resolution X-ray diffraction (HRXRD) (002) ω-scans rocking curves of as grown GaN and porous GaN samples annealed at 1150 °C for different times 30min, 45min, 60min, 75min, 90min, 105min.

Figure S3. High-resolution X-ray diffraction (HRXRD) (002) ω-scans rocking curves of as grown GaN and porous GaN samples annealed at 1150 °C for different times 30min, 45min, 60min, 75min, 90min, 105min.